

Attorney Docket No.: 0180197

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

OCT 21 2004

In re Application of: Bin Yu**Serial No.: 09/826,472****Filed: April 4, 2001****For: Method of Fabricating a Semiconductor
Device Having a Nitride/High-k/Nitride
Gate Dielectric Stack by Atomic Layer
Deposition (ALD) and a Device Thereby
Formed****Art Unit: 2812****Examiner: Pompey, Ron Everett****RESPONSE TO FINAL OFFICE ACTION**

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the *Final Office Action* dated September 22, 2004 in the above-referenced patent application. Please enter and consider the following remarks.